TOSHIBA MT6P07T

TOSHIBA TRANSISTOR SILICON NPN EPITAXIAL PLANAR TYPE

VHF~UHF BAND LOW NOISE AMPLIFIER APPLICATIONS

TWO devices are built in to the super-thin and ultra super mini (6 pins) package: TU6

MOUNTED DEVICES

	Q1/Q2 : SSM (TESM)
Three-pins (SSM/TESM) mold products are corresponded.	MT3S07S (MT3S07T)

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	Q1 / Q2	UNIT	
Collector-Base Voltage	v_{CBO}	10	V	
Collector-Emitter Voltage	v_{CEO}	5	V	
Emitter-Base Voltage	$v_{ m EBO}$	1.5	V	
Collector Current	$_{ m I_C}$	25	mA	
Base Current	$I_{\mathbf{B}}$	10	mA	
Collector Power Dissipation	P _C (Note 1)	200	mW	
Junction Temperature	T_{j}	125	°C	
Storage Temperature Range	$ m T_{stg}$	-55~125	°C	

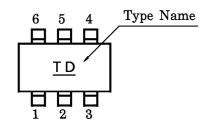
 2.1 ± 0.1 1.25 ± 0.1 2.0 ± 0.2 1.3 ± 0.1 1. EMITTER 1 4. COLLECTOR 2 2. EMITTER 2 5. BASE 1 BASE 2 COLLECTOR 1 **JEDEC EIAJ TOSHIBA** 2-2JA1A

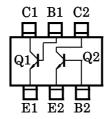
Unit in mm

(Note 1): Total power dissipation of Q1 and Q2.

MARKING

PIN ASSIGNMENT (TOP VIEW)





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ELECTRICAL CHARACTERISTICS Q1/Q2 (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	ICBO	$V_{CB} = 5 \text{ V}, I_{E} = 0$	_	_	0.1	μ A
Emitter Cut-off Current	$I_{ m EBO}$	$V_{EB} = 1 V, I_{C} = 0$	_	_	1	μ A
DC Current Gain	${ m h_{FE}}$	$V_{CE} = 1 V$, $I_{C} = 5 mA$	70	_	140	_
Transition Frequency	${ m f_T}$	$V_{ m CE}=3~{ m V},~{ m I}_{ m C}=10~{ m mA}$	10	12	_	GHz
Insertion Gain	$ S_{21e} ^2(1)$	$V_{\text{CE}} = 1 \text{ V}, \text{ I}_{\text{C}} = 5 \text{ mA},$ $f = 2 \text{ GHz}$	_	7	_	dB
	$ S_{21e} ^2$ (2)	$V_{CE} = 3 \text{ V}, I_{C} = 15 \text{ mA}, $ f = 2 GHz	6.5	8.5	_	dB
Noise Figure	NF (1)	$V_{CE} = 1 \text{ V}, I_{C} = 5 \text{ mA},$ f = 2 GHz		1.6	3	dB
	NF (2)	$V_{CE} = 3 \text{ V}, I_{C} = 5 \text{ mA},$ f = 2 GHz		1.5	3	dB
Reverse Transfer Capacitance	$\mathrm{C_{re}}$	$V_{CB} = 1 V, I_{E} = 0, f = 1 MHz$ (Note 2)		0.45	0.85	pF

(Note 2): C_{re} is measured by 3 terminal method with capacitance bridge.

HANDLING PRECAUTION

When handling individual devices (which are not yet mounting on a circuit board), be sure that the environment is protected against electrostatic electricity. Operators should wear anti-static clothing, and containers and other objects that come into direct contact with devices should be made of anti-static materials.